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1-22-03
PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Mitsutoshi MIYASAKA

Application No.: 09/885,027

Filed: June 21, 2001

For: THE THIN FILM SEMICONDUCTOR DEVICE ITSELF, LIQUID CRYSTAL
DISPLAY, AND ELECTRONIC DEVICE

Group Art Unit: 2815

Examiner: J. Jackson

Docket No.: 36654.04

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AMENDMENT UNDER 37 C.F.R. §1.111

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the August 20, 2002 Office Action, the period for reply extended to
January 21, 2003, by a Petition for Extension Time, filed herewith, please amend the above-
identified application as follows:

IN THE CLAIMS:

Please replace claims 1 and 2 as follows:

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1. (Amended) A thin film semiconductor device, comprising:
a substrate;
an underlevel protection layer formed over the substrate and including a
plurality of films, at least one of which includes a silicon oxide; and
a crystallized semiconductor layer in contact with the film including the
silicon oxide, wherein the crystallized semiconductor layer forms an active layer of a
transistor,
an effective doping concentration of the crystallized semiconductor layer
figuring $1 \times 10^{18} \text{ cm}^{-3}$ or less and the crystallized semiconductor layer having the thickness of